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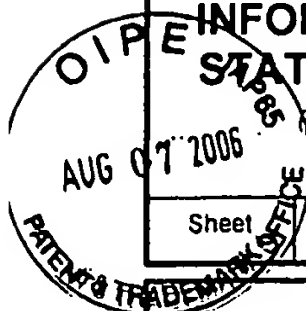
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Substitute for form 1449A/PTO			<b>Complete if Known</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (Use as many sheets as necessary)			Application Number	09/535,015
			Filing Date	March 24, 2000
			First Named Inventor	Shunpei YAMAZAKI et al.
			Group Art Unit	2811
			Examiner Name	Sara W. Crane
Sheet 1	of 2	Attorney Docket Number	0756-2131	



FOREIGN PATENT DOCUMENTS								
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)				
SC		EP	0 178 447		—	04/23/1986	—	Eng.

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
SC		STOEMENOS et al., <i>Crystallization of Amorphous Silicon by Reconstructive Transformation Utilizing Gold</i> , Appl. Phys. Lett., Volume 58, No. 11, March 18, 1991, Pages 1196-1198.	
		KUZNETSOV et al., <i>Enhanced Solid Phase Epitaxial Recrystallization of Amorphous Silicon Due to Nickel Silicide Precipitation Resulting from Ion Implantation and Annealing</i> , Nuclear Instruments and Methods in Physics Research, 880/881, 1993, Pages 990-993.	
		HATALIS et al., <i>High Performance Thin-Film Transistors in Low Temperature Crystallized LPCVD Amorphous Silicon Films</i> , IEEE Electron Device Letters, Vol. EDL 8, No. 8, August 1987, Pages 361-364.	
		LAU et al., <i>Solid Phase Epitaxy Silicide-Forming Systems</i> , Thin Solid Films, Volume 47, No. 3, 1977, Pages 313-322.	
		KAWAZU et al., <i>Initial Stage of the Interfacial Reaction Between Nickel and Hydrogenated Amorphous Silicon</i> , Japanese Journal of Applied Physics, Volume, 29, No. 4, April 1, 1990, Pages 729-738.	
		HEMPEL et al., <i>Needle-Like Crystallization of Ni Doped Amorphous Silicon Thin Films</i> , Solid State Communications, Volume 85, No. 11, 1993, Pages 921-924.	
		KUO, <i>PD Introduced Lateral Crystallization of Amorphous Silicon Thin Films at Low Temperature</i> , Thin Film Transistor Technologies, Volume 94-35, Pages 116-122, April, 1995.	
		WOLF et al., <i>Silicon Processing for the VLSI Era</i> , Volume 1: Process Technology, Lattice Press, 1986, Pages 207-211.	
SC		DVURECHENSKII et al., <i>Transport Phenomena in Amorphous Silicon Doped by Ion Implantation of 3d Metals</i> , Phys. Stat. Sol. (a), Volume 95, No. 635, 1986, Pages 635-640.	

Examiner Signature	/Sara Crane/	Date Considered	08/30/2006, 9/13/2006
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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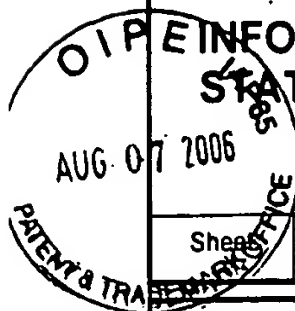
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SC		HAYZELDEN et al., <i>Silicide Formation and Silicide Mediated Crystallization of Nickel-Implanted Amorphous Silicon Thin Films</i> , J. Appl. Phys., Volume 73, No. 12, June 15, 1993, Pages 8279-8289.	
↓		KUZNETSOV et al., <i>Silicide Precipitate Formation and Solid Phase Re-Growth of Ni<sup>+</sup>-Implanted Amorphous Silicon</i> , Inst. Phys. Conf. Ser. No. 134.4: Proceedings of the Royal Microscopical Society Conf., April 5-8, 1993, Pages 191-194.	
↓		BAKER, JR. et al., <i>Field Effect Transistor</i> , IBM Technical Disclosure Bulletin, Volume 11, No. 7, December 1968, Page 849.	
↓		WOLF, <i>Silicon Processing for the VLSI Era</i> , Volume 2: Process Integration, 1990, Pages 273-274.	
SC		CAUNE et al., <i>Combined CW Laser and Furnace Annealing of Amorphous Si and Ge in Contact with Some Metals</i> , Applied Surface Science, Volume 36, January 1, 1989, Pages 597-604.	

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